



**Advanced Power
Electronics Corp.**

AP95N25W

RoHS-compliant Product

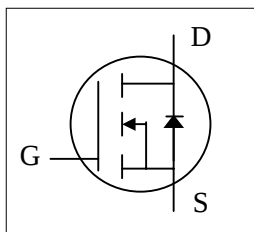
N-CHANNEL ENHANCEMENT MODE

POWER MOSFET

▼ Simple Drive Requirement

▼ Lower On-resistance

▼ High Speed Switching

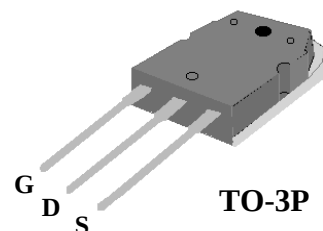


BV_{DSS}	250V
$R_{DS(ON)}$	55m Ω
I_D	50A

Description

AP95N25 from APEC provide the designer with the best combination of fast switching , low on-resistance and cost-effectiveness .

The TO-3P package is preferred for commercial & industrial applications with higher power level preclusion than TO-220 device.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	250	V
V_{GS}	Gate-Source Voltage	± 30	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V	50	A
I_{DM}	Pulsed Drain Current ¹	200	A
I_{DR}	Body-Drain Diode Reverse Drain Current	50	A
$I_{DR(PULSE)}$	Body-Drain Diode Reverse Drain Peak Current ¹	200	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation	150	W
	Linear Derating Factor	1.2	W/ $^{\circ}C$
I_{AR}	Avalanche Current ³	30	A
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Thermal Resistance Junction-case	Max. 0.833	$^{\circ}C/W$
Rthj-a	Thermal Resistance Junction-ambient	Max. 40	$^{\circ}C/W$



AP95N25W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =1mA	250	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =25A	-	-	55	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	2.5	-	4	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =25A	-	25	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =250V, V _{GS} =0V	-	-	1	uA
I _{GSS}	Gate-Source Leakage	V _{GS} = ±30V, V _{DS} =0V	-	-	±0.1	uA
Q _g	Total Gate Charge ²	I _D =50A	-	168	270	nC
Q _{gs}	Gate-Source Charge	V _{DS} =200V	-	36	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =10V	-	68	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =125V	-	50	-	ns
t _r	Rise Time	I _D =25A	-	92	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =10Ω, V _{GS} =10V	-	250	-	ns
t _f	Fall Time	R _D =5Ω	-	105	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	8370	13400	pF
C _{oss}	Output Capacitance	V _{DS} =15V	-	1505	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	60	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =50A, V _{GS} =0V	-	-	1.5	V
t _{rr}	Reverse Recovery Time ²	I _S =50A, V _{GS} =0V	-	320	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	4.7	-	μC

Notes:

1. PW ≤ 10us, duty cycle ≤ 1%
2. Pulse test
3. STch = 25°C · Tch ≤ 150°C

THIS PRODUCT IS AN ELECTROSTATIC SENSITIVE, PLEASE HANDLE WITH CAUTION.

THIS PRODUCT HAS BEEN QUALIFIED FOR CONSUMER MARKET. APPLICATIONS OR USES AS CRITERIAL COMPONENT IN LIFE SUPPORT DEVICE OR SYSTEM ARE NOT AUTHORIZED.

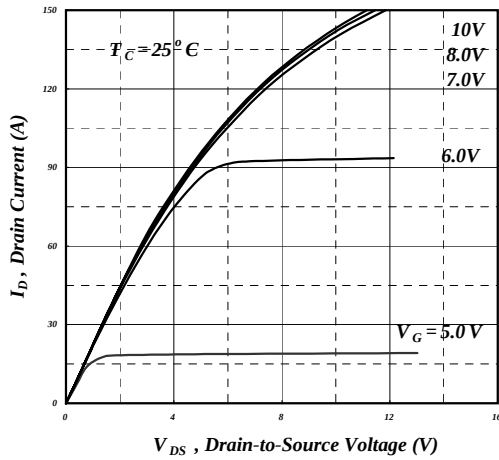


Fig 1. Typical Output Characteristics

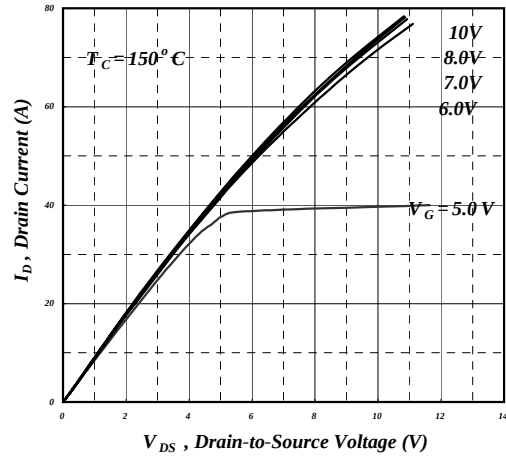


Fig 2. Typical Output Characteristics

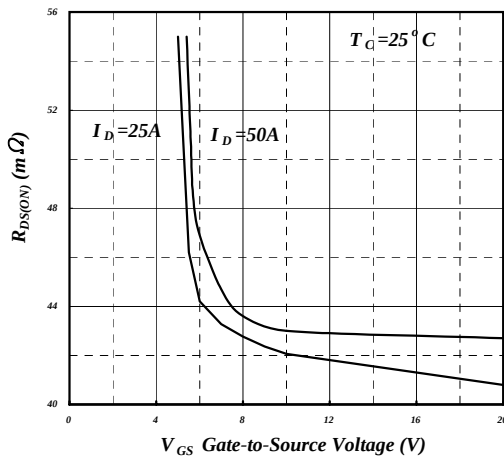


Fig 3. On-Resistance v.s. Gate Voltage

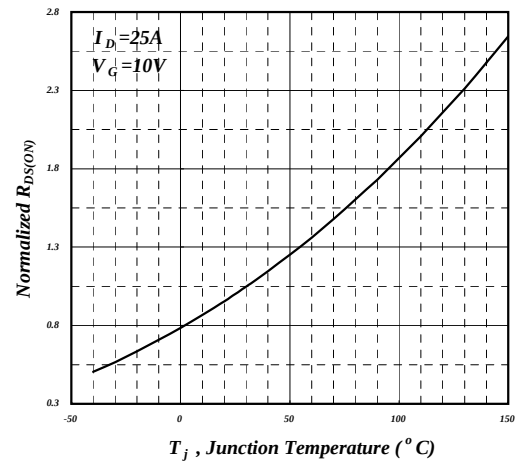


Fig 4. Normalized On-Resistance v.s. Junction Temperature

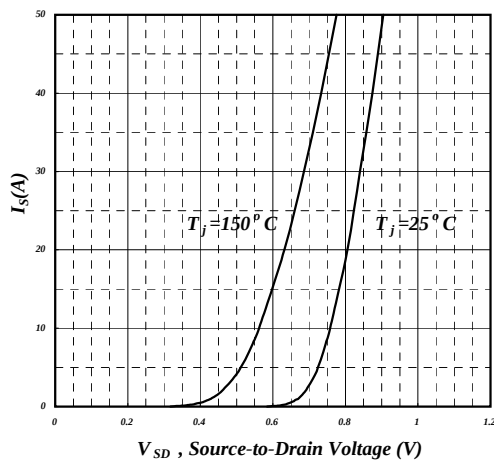


Fig 5. Forward Characteristic of Reverse Diode

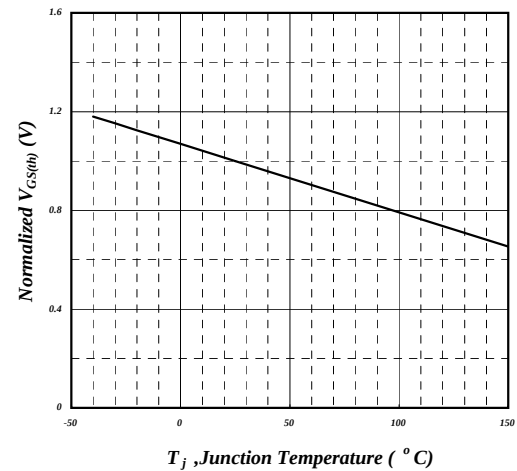


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

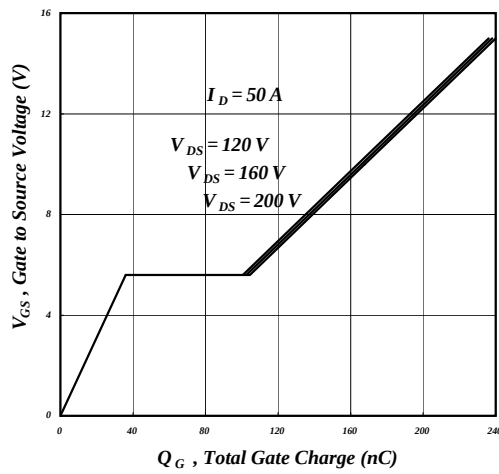


Fig 7. Gate Charge Characteristics

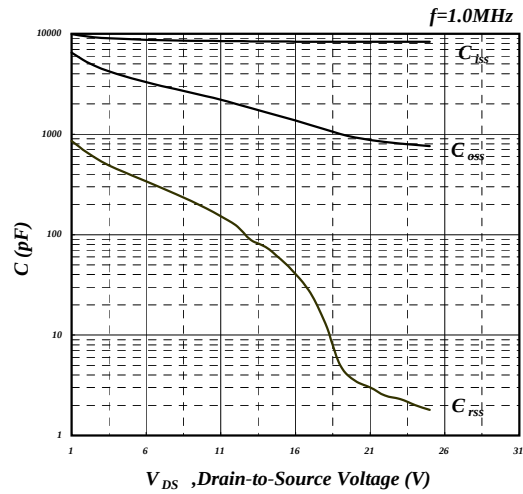


Fig 8. Typical Capacitance Characteristics

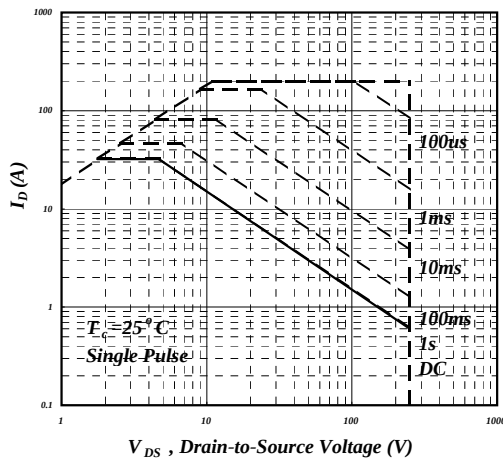


Fig 9. Maximum Safe Operating Area

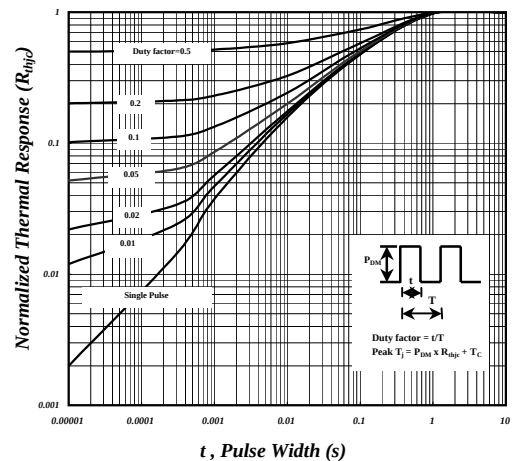


Fig 10. Effective Transient Thermal Impedance

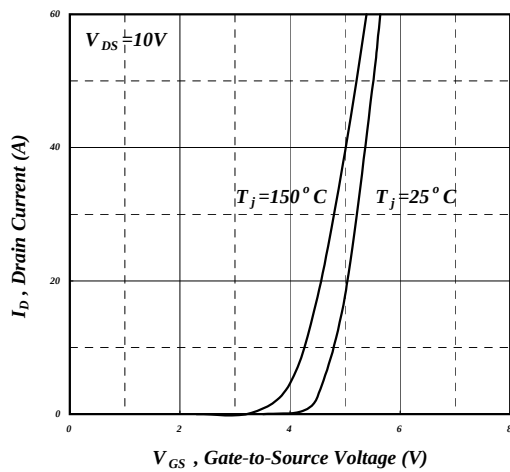


Fig 11. Transfer Characteristics

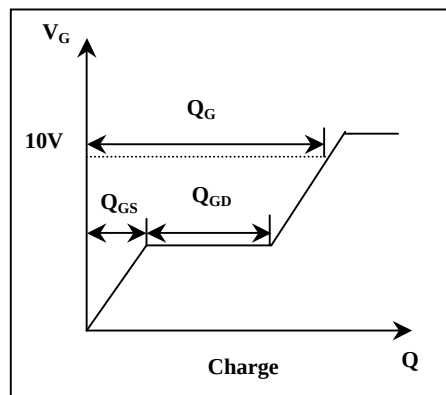


Fig 12. Gate Charge Waveform